Plasma Processing 20

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Plasma Processing 20

Table of Contents

Preface *iii*

Alternative to H_3PO_4 for Si_3N_4 Removal by Using Chemical Downstream Etching 1
C. de Buttet, O. Gourhant, R. Bouyssou, S. Zoll

HfO_2 Gate Stack Engineering by Post-Gate Cleaning Using NF_3/NH_3 Plasma 11
M. S. Lee, H. J. Oh, J. H. Lee, I. G. Lee, W. G. Shin, S. Y. Kang, D. H. Ko

Author Index 17